



GaNSlim™ HFQR/CCM Control

1. Features

GaNSlim™ Power FET

- Loss-less current sensing
- Low R_{dson} power FET
- Zero reverse recovery charge
- Low output charge
- 800 V Transient Voltage Rating
- 700 V Continuous Voltage Rating

High Frequency QR/CCM Controller

- Wide VDD range up to 77.5V
- QR valley switching and CCM operating modes
- High frequency operation
- High voltage start-up
- Optimized driver and frequency hopping for low EMI
- OVP, UVP, OTP, LPS protection functions
- Ultra-low standby current consumption

DPAK-4L Package with Grounded Cooling Pad

- Minimized package inductance
- Low thermal resistance

High Power Density

- High power density
- Small transformer size
- Low component count

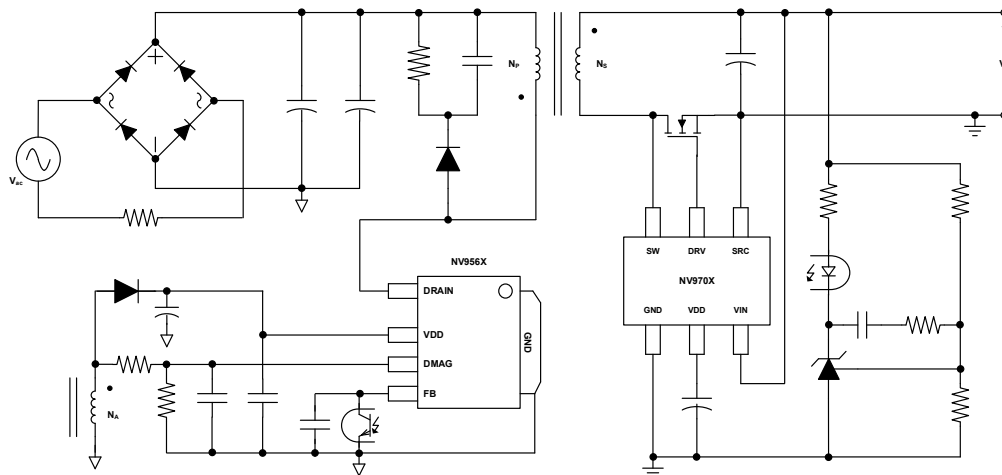
Product Reliability

- 20-year limited product warranty (see Section 14 for details)

2. Topologies / Applications

- High efficiency AC-DC power adapters
- USB PD/QC battery charger
- Auxiliary power for servers, white goods.

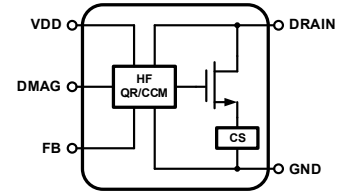
4. Typical Application Circuit



Flyback Application Schematic



DPAK-4L



Simplified schematic

3. Description

This GaNSlim™ HFQR/CCM controller integrates a high performance eMode GaNSlim Power FET together with an HFQR/CCM Flyback controller to achieve unprecedented high-frequency and high-efficiency operation for smallest size mobile charger and adapter solutions. The GaNSlim Power FET includes loss-less current sensing, ultra-low gate charge, low output charge, and 700V continuous and 800V transient voltage ratings to provide excellent performance and robustness. The HFQR/CCM Flyback controller enables high frequency operation, wide VDD range, high-voltage start-up, and multi-mode operation. The HFQR/CCM Flyback controller also includes abnormal component short-circuit, over-temperature and LPS protection features to increase system robustness, while ultra-low standby current consumption increases light, tiny & no-load efficiency. Low-profile, low-inductance, and DPAK-4L packaging enables designers to achieve simple, quick and reliable solutions. Navitas' GaN IC technology enables high frequencies, high efficiencies, and low EMI to achieve unprecedented power densities at a very attractive cost structure.

5. Table of Contents

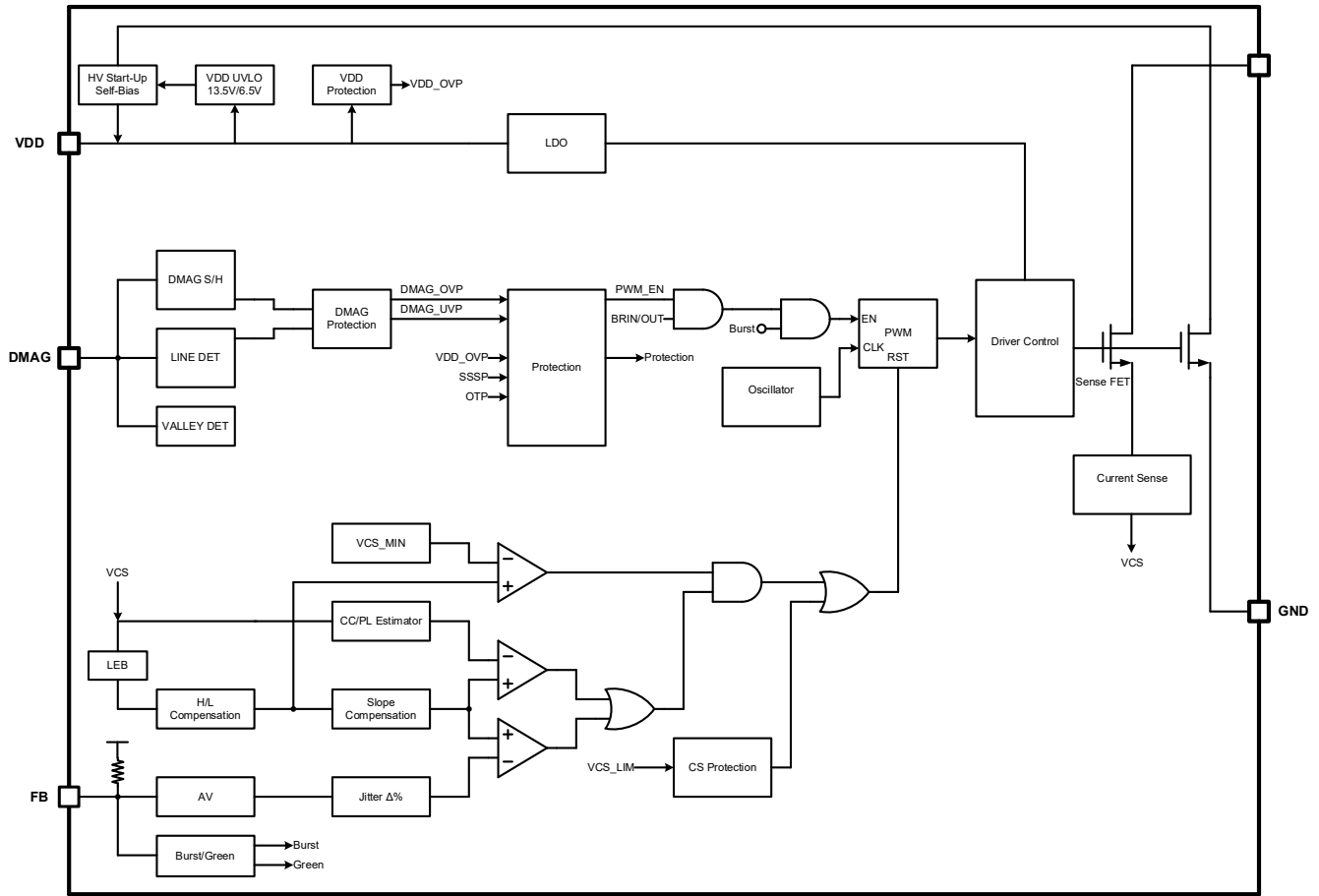
1. Features	1	Electrical Specifications (cont.)	9
2. Topologies / Applications	1	Electrical Specifications (cont.)	10
3. Description	1	8.5. Characteristic Graphs	11
4. Typical Application Circuit	1	Characteristic Graphs (cont.)	12
5. Table of Contents	2	Characteristic Graphs (Cont.)	13
6. Ordering Information	3	Characteristic Graphs (Cont.)	14
7. Internal Functional Block Diagram	4	9. Pin Configurations and Functions	15
8. Specifications	5	10. Functional Description	16
8.1. Absolute Maximum Ratings ⁽¹⁾	5	11. Package Outline (DPAK-4L)	23
8.2. Recommended Operating Conditions ⁽⁴⁾	6	12. Tape and Reel Dimensions	25
8.3. Thermal Resistance ⁽⁵⁾	6	13. 20-Year Limited Product Warranty	27
8.4. Electrical Specifications	7	14. Revision History	27
Electrical Specifications (cont.)	8		

6. Ordering Information

Part Number	Maximum Frequency	$R_{DS(ON)}$	Typ. Internal R_{cs} (Ω)	Typ. Primary Current Limit I_p (A)	Mode & Protection	Operating Temperature Range	Package	Packing Method Tape & Reel
NV9562L35C	125kHz	260m Ω	1350	2.76	QR LAR	-40°C to +125°C	DAPK- 4L	2,000: 13" Reel

LAR: Long Auto-Restart Mode

7. Internal Functional Block Diagram



8. Specifications

8.1. Absolute Maximum Ratings ⁽¹⁾

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit	
V _{DS(CONT)}	GaN Power FET Continuous Drain-to-Source Voltage ⁽²⁾	-7	700	V	
V _{DS(TRAN)}	GaN Power FET Transient Drain-to-Source Voltage ⁽³⁾	-	800	V	
V _{VDD}	VDD DC Supply Voltage	-0.3	80	V	
V _{FB}	FB Pin Input Voltage	-0.3	5.5	V	
V _{DMAG}	DMAG Pin Input Voltage	-0.3	5.5	V	
I _D	GaN Power FET Continuous Drain Current. (@T _C = 100°C)	-	5	A	
I _D PULSE	GaN Power FET Pulsed Drain Current (10 μs @ T _J = 125°C)	-	10	A	
T _J	Operating Junction Temperature	-40	150	°C	
T _{STG}	Storage Temperature Range	-40	150	°C	
T _L	Lead Temperature (Soldering) 10 Seconds	-	260	°C	
ESD	Electrostatic Discharge Capability	Human Body Mode, ANSI/ESDA/JEDEC JS-001-2024		1.5	kV
		Charge Device Mode, ANSI/ESDA/JEDEC JS-002-2025	-	1.0	kV

Note (1): Stress beyond those listed under absolute maximum ratings may cause permanent damage to the device

Note (2): V_{DS(CONT)} rating is specified for GaN Power FET

Note (3): V_{DS(TRAN)} rating is specified for GaN Power FET and allows for surge ratings during non-repetitive events that are <100us (for example start-up, line interruption) and repetitive events that are <400ns (for example repetitive leakage inductance spikes).

8.2. Recommended Operating Conditions ⁽⁴⁾

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance. Navitas does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{VDD}	VDD Pin Supply Voltage	-0.3		75	V
V _{FB}	FB Pin Supply Voltage	-0.3		5	V
V _{DMAG}	DMAG Pin Supply Voltage	-0.3		5	V

Note (4): Functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions are not implied, exposure to absolute maximum rated conditions of extended periods may affect device reliability. All voltage values are with respect to the normal operation ambient temperature range is from -40°C to +125°C unless otherwise noted.

8.3. Thermal Resistance ⁽⁵⁾

Symbol	Parameter	Typ.	Unit
R _{θJA}	Junction-to-Case	6.86	°C/W
R _{θJC}	Junction-to-Ambient	50.09	°C/W

Note (5) R_θ measured on DUT mounted on 1 square inch 2 oz Cu (FR4 PCB)

8.4. Electrical Specifications

V_{DD} (Typ.) = 12V, and T_A (Typ.) = 25°C, unless otherwise specified.

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
HV Section						
I_{HV}	Supply Current Drawn from Drain Pin	$V_{DRAIN}=50\text{ V}, V_{DD}=0\text{ V}$	2	5	10	mA
I_{HV-LC}	Leakage Current Drawn from Drain Pin	$V_{DRAIN}=50\text{ V}, V_{DD}=V_{DD_UVLO}+1\text{ V}$			3	μA
VDD Section						
V_{DD_ON}	V_{DD} Turn-On Threshold Voltage	V_{DD} Rising	12.0	13.5	15.0	V
V_{DD_UVLO}	V_{DD} UVLO Threshold Voltage		6.3	6.5	6.8	V
I_{DD_ST}	Startup Current		0.5	2	5	μA
I_{DD_OP}	Operating Supply Current	No DRV Switching	0.60	0.75	0.85	mA
I_{DD_DPGN}	Operating Supply Current in Deep Green-Mode		200	300	400	μA
$V_{DD_OVP}^{(6)}$	V_{DD} Over-Voltage-Protection Threshold		77	78.5	80	V
$t_{D_UVLO}^{(6)}$	UVLO De-bounce Time			10		μs
$t_{D_VDD_OVP}^{(6)}$	V_{DD} Over-Voltage-Protection De-bounce Time			15		μs
t_{VDD_LAR}	Long Auto-Restart Mode Time	Trim Option	1.38	1.64	1.90	s
Oscillator Section						
f_{S_TMO}	Minimum Time-Out Frequency		24	25	26	kHz
f_{S_CRM}	Minimum CRM Frequency		14.2	15.6	17	kHz
$f_{S_BNK_MAX}$	Maximum Blanking Frequency	Option:125kHz	115	125	135	kHz
		Option:175kHz	160	175	190	kHz
		Option:225kHz	205	225	245	kHz
$f_{S_CCM_MAX}$	Maximum CCM Frequency	Option:125kHz	95.9	104	112.5	kHz
		Option:175kHz	133.4	145.8	158.2	kHz
t_{ON_MAX}	Maximum PWM ON Time Opt1	Option:125kHz	16.2	17.6	19	μs
		Option:175kHz, 225kHz	8.6	9.6	10.6	μs
D_{MAX}	Maximum Duty Cycle in CCM	While CCM is disabled, no D_{MAX} $V_{OSC_DMAX}=0.625\text{V}$	71	75	79	%
ΔV_{JIT}	Current Sense of Jitter Range	Low line High line		+/-3.85 +/-7.7		%
t_{JIT}	Frequency Jitter Period		0.5	0.60	0.7	ms
Δf_{JIT_CCM}	CCM Jitter Range			+/-3.85		%

Electrical Specifications (cont.)

V_{DD} (Typ.) = 12V, and T_A (Typ.) = 25°C, unless otherwise specified.

Parameter		Test Conditions	Min.	Typ.	Max.	Unit
Feedback Section						
V _{FB_OPEN}	FB Open Voltage		5.00	5.20	5.40	V
Z _{FB}	FB Pull Up Resistor		36	40	48	kΩ
A _V ⁽⁶⁾	FB Voltage Attenuation Factor	Default	0.185	0.200	0.215	V/V
V _{FB_GRN_ENT}	FB Threshold for Green Mode Entry		1.550	1.600	1.650	V
V _{FB_GRN_EXT}	FB Threshold for Green Mode Exit		1.650	1.700	1.750	V
V _{FB_BST_ENT}	FB Threshold for Burst Mode Entry		0.650	0.700	0.750	V
V _{FB_BST_EXT}	FB Threshold for Burst Mode Exit		0.700	0.750	0.800	V
V _{FB_BNK_STR}	Frequency Foldback Start Point		2.225	2.300	2.375	V
V _{FB_BNK_END_125kHz}	Frequency Foldback End Point	Option:125kHz, 175kHz	1.475	1.550	1.625	V
V _{FB_BNK_END_225kHz}	Frequency Foldback End Point	Option:225kHz	1.425	1.500	1.575	V
t _{D_DPGN}	Debounce Time to Enter Deep Green Mode		120	160	200	μs
V _{FB_OLP}	FB Threshold for OLP Exit		3.5	3.6	3.7	V
	FB Threshold for OLP Enter		3.8	3.9	4.0	V
t _{D_OLP}	OLP Protection De-bounce Time		32	36	40	ms
Over-Temperature Protection Section						
T _{OTP}	Over-Temperature-Protection Threshold		125	140	155	°C
ΔT _{OTP} ⁽⁶⁾	Over-Temperature-Protection Hysteresis			20		°C

Electrical Specifications (cont.)
 V_{DD} (Typ.) = 12V, and T_A (Typ.) = 25°C, unless otherwise specified.

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
DMAG Section					
I_{DMAG_Max}	Maximum Guaranteed Operating Current Flow Out of DMAG Pin	1.94			mA
I_{DMAG_BRI}	Current Threshold for Brown-In	0.432	0.480	0.528	mA
N_{BRI}	Debounce Cycle for Brown-In		4		Cycle
I_{DMAG_BRO}	Current Threshold for Brown-Out	0.396	0.440	0.484	mA
t_{D-BRO}	Debounce Cycle for Brown-Out	15	16.5	18	ms
I_{DMAG_HL}	Current Threshold for High Line (164V _{AC})	1.008	1.120	1.232	mA
N_{HL_ENT}	Debounce Cycle for High Line Entry		4		Cycle
I_{DMAG_LL}	Current Threshold for Low Line (153V _{AC})	0.936	1.04	1.144	mA
t_{D-LL_ENT}	Debounce Cycle for Low Line Entry	15	16.5	18	ms
V_{DMAG_HV}	V_{DMAG} Threshold for High Output	1.65	1.75	1.85	V
V_{DMAG_LV}	V_{DMAG} Threshold for Low Output	1.50	1.60	1.70	V
$V_{DMAG_LV_HYS}$	V_{DMAG} Hysteresis Threshold for Low Output		0.150		V
$N_{DMAG_HV_LV}$	Debounce Cycle for High/Low Output Change		4		Cycle
V_{DMAG_UVP}	V_{DMAG} Under-Voltage-Protection Threshold	0.390	0.425	0.460	V
N_{DMAG_UVP}	Debounce Cycle for V_{DMAG_UVP}		2		Cycle
$t_{VDMAG_UVP_BNK}$	V_{DMAG_UVP} Blanking Time during Start-up	27.5	32	36.5	ms
V_{DMAG_OVP}	V_{DMAG} Over-Voltage-Protection Threshold	3.45	3.55	3.65	V
N_{DMAG_OVP}	Debounce Cycle for V_{DMAG_OVP}		2		Cycle
$t_{DMAG_BNK_L}$	DAMG Sampling Blanking Time $V_{FB} < V_{FB_GRN_ENT}$ (1.60V)	Option: 125kHz	0.96		μs
		Option: 175kHz, 225kHz	0.48		μs
$t_{DMAG_BNK_M}$	DAMG Sampling Blanking Time $V_{FB} > V_{FB_GRN_EXT}$ (1.70V)	Option: 125kHz	1.6		μs
		Option: 175kHz, 225kHz	1.07		μs

Electrical Specifications (cont.)
 V_{DD} (Typ.) = 12V, and T_A (Typ.) = 25°C, unless otherwise specified.

Parameter		Test Conditions	Min.	Typ.	Max.	Unit
Current Sense Section						
Gain _{CS}	Current Sense Ratio I_{CS}/I_{DRAIN}			5725		A/A
R _{EFF}	Effective Sense Resistor			R _{CS} /Gain _{CS}		Ω
I _p	Primary Current Limit	R _{CS} =1350	2.51	2.76	3.01	A
I _{BST}	Primary Current at Burst Mode			0.385*I _p		A
t _{LEB}	Leading Edge Blanking Time			265		ns
t _{PD}	Propagation Delay from CS to DRV			65		ns
GaN Power FET Section						
Typical conditions: $V_{DS} = 400V$, $F_{SW} = 1MHz$, $T_{AMB} = 25^{\circ}C$, unless otherwise specified						
I _{DSS}	Drain-Source Leakage Current	$V_{DS} = 650V$, FET OFF		0.15	25	μA
R _{DS(ON)}	Drain-Source Resistance			260	364	mΩ
V _{SD}	Source-Drain Reverse Voltage			3.5		V
Q _{OSS}	Output Charge	$V_{DS} = 400V$, FET OFF		11.2		nC
Q _{RR}	Reverse Recovery Charge			0		nC
C _{OSS}	Output Capacitance	$V_{DS} = 400V$, FET OFF		15		pF
C _{O(er)} ⁽⁷⁾	Effective Output Capacitance, Energy Related	$V_{DS} = 400V$, FET OFF		20		pF
C _{O(tr)} ⁽⁷⁾	Effective Output Capacitance, Time Related	$V_{DS} = 400V$, FET OFF		28		pF

Note (6): Guaranteed by design

Note (7): $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 400 V

$C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 400 V

8.5. Characteristic Graphs

($T_C = -40$ to 125 °C unless otherwise specified)

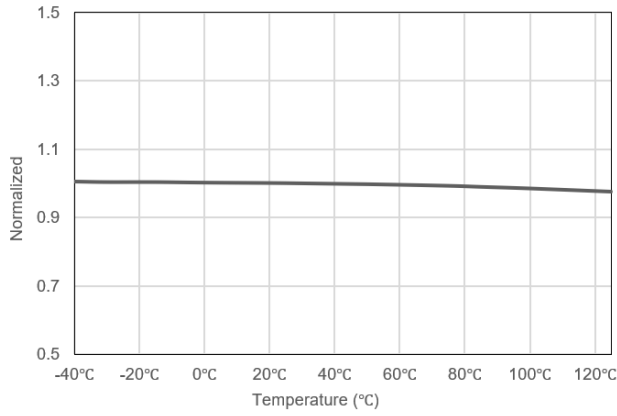


Fig. 1. V_{DD_ON}

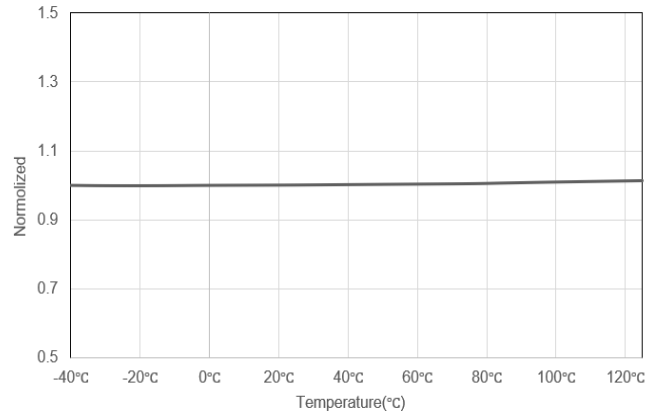


Fig. 2. V_{DD_UVLO}

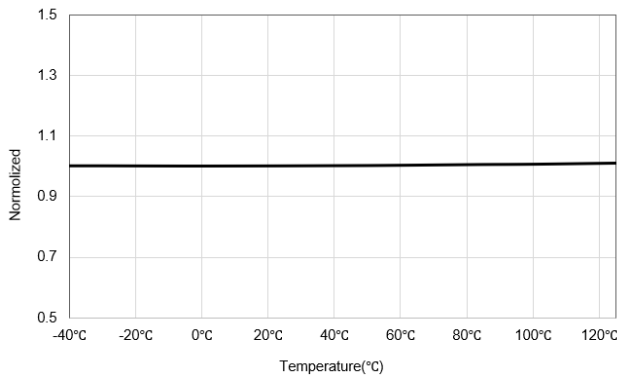


Fig. 3. V_{DD_OVP}

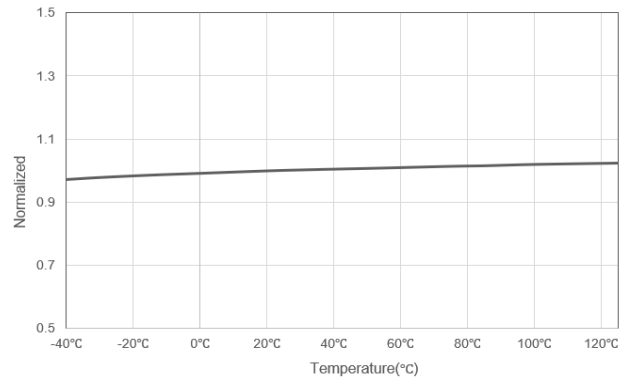


Fig. 4. f_{s_TMO}

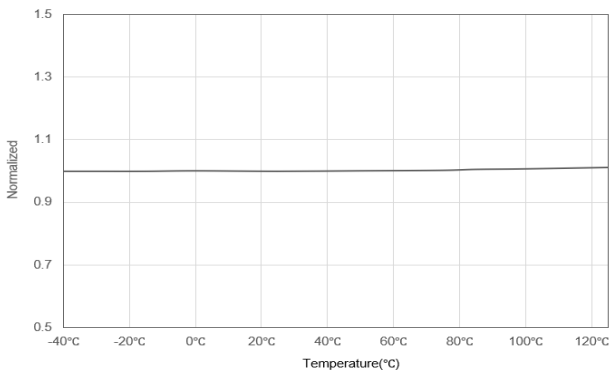


Fig. 5. V_{FB_BST_ENT}

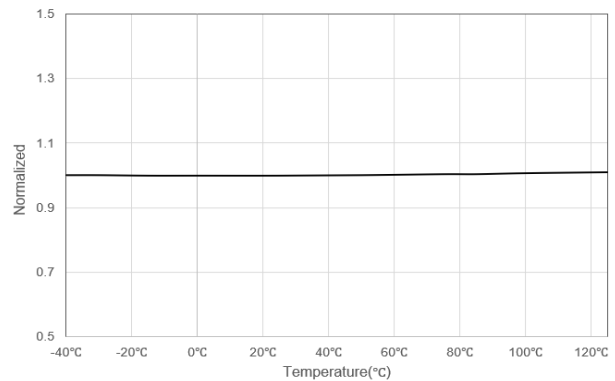


Fig. 6. V_{FB_BST_EXT}

Characteristic Graphs (cont.)

($T_C = -40$ to 125 °C unless otherwise specified)

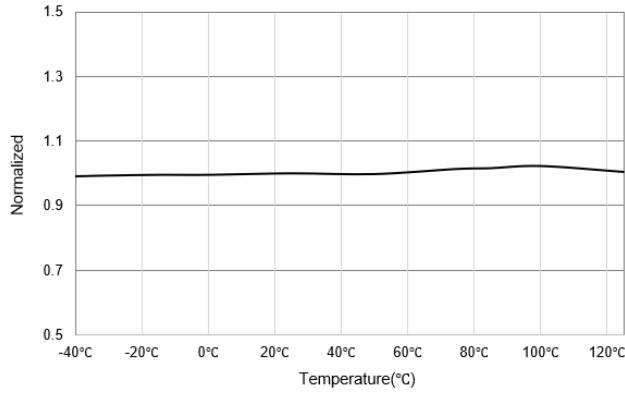


Fig. 7. IdMAG_BRI

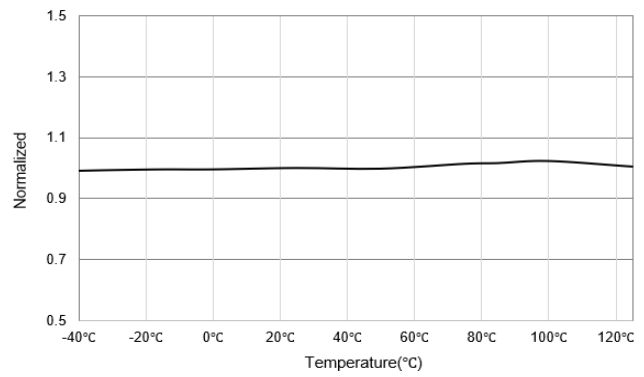


Fig. 8. IdMAG_BRO

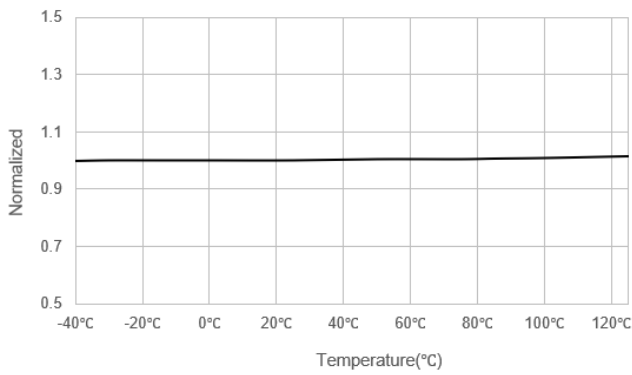


Fig. 9. VDMAG_UVP

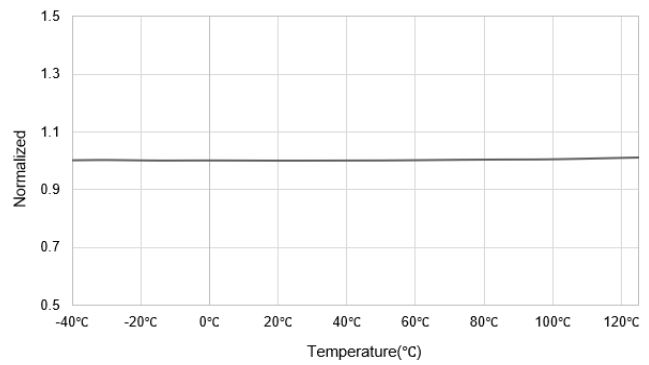


Fig. 10. VDMAG_OVP

Characteristic Graphs (Cont.)

($T_C = 25\text{ }^\circ\text{C}$ unless otherwise specified)

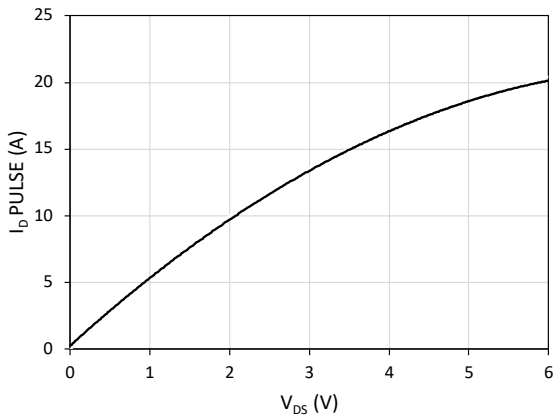


Figure 11. Pulsed Drain current (I_D PULSE) vs. drain-to-source voltage (V_{DS}) at $T = 25\text{ }^\circ\text{C}$

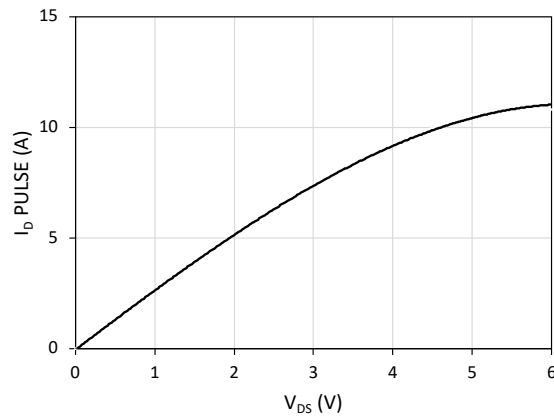


Fig.12. Pulsed Drain current (I_D PULSE) vs. drain-to-source voltage (V_{DS}) at $T = 125\text{ }^\circ\text{C}$

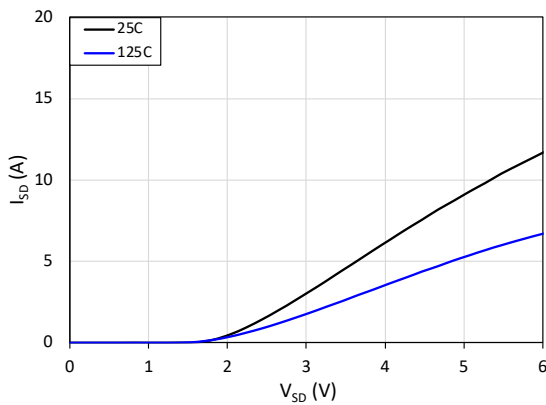


Figure 13. Source-to-drain reverse conduction voltage

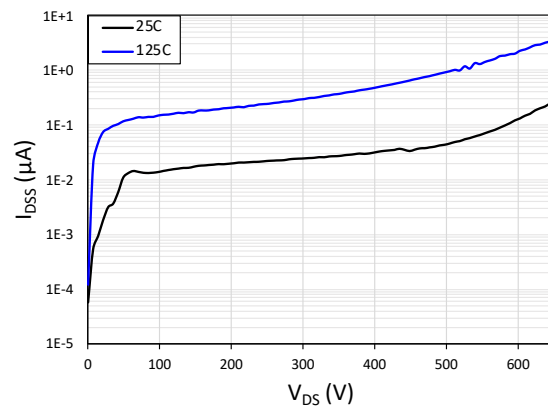


Figure 14. Drain-to-source leakage current (I_{DSS}) vs. drain-to-source voltage (V_{DS})

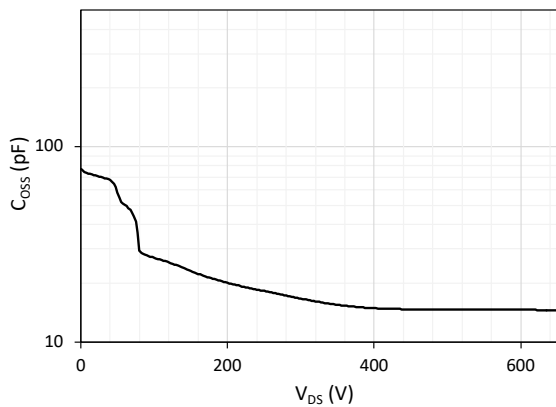


Figure 15. Output capacitance (C_{OSS}) vs. drain-to-source voltage (V_{DS})

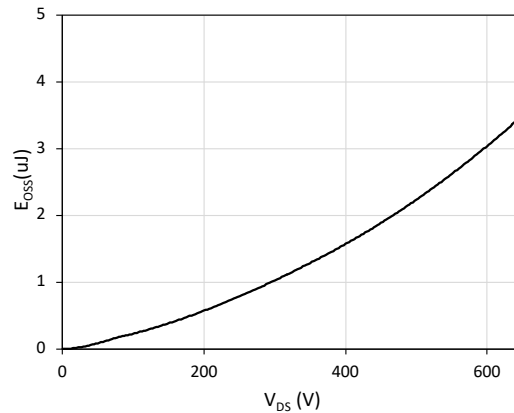


Figure 16. Energy stored in output capacitance (E_{OSS}) vs. drain-to-source voltage (V_{DS})

Characteristic Graphs (Cont.)

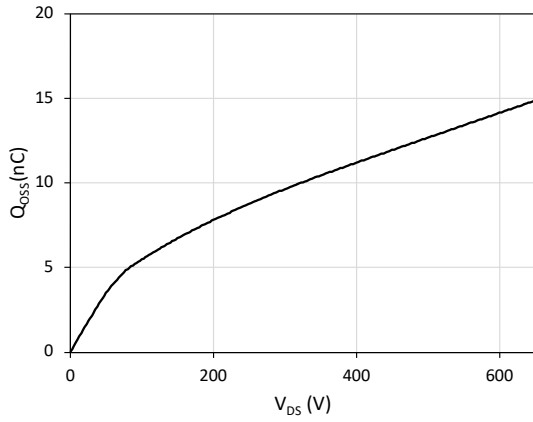


Figure 17. Charge stored in output capacitance (Q_{OSS}) vs. drain-to-source voltage (V_{DS})

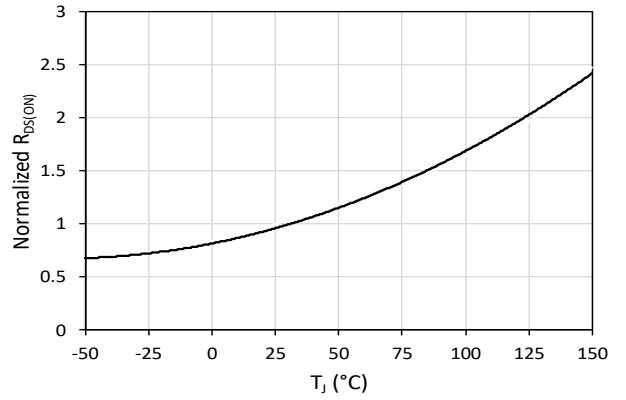


Figure 18. Normalized on-resistance ($R_{DS(ON)}$) vs. Junction temperature (T_J)

9. Pin Configurations and Functions

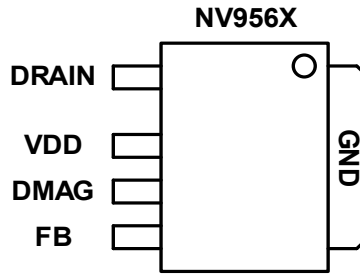


Fig. 19. Pin Configuration (Top View)

Pin No.	Name	Description
1	DRAIN	Drain of GaN Power FET. This pin is also connected internally to the high-voltage startup circuit.
2	VDD	Power Supply. IC operation current and GaN FET driving current are supplied through this pin. Typically, this pin is connected to an external V _{DD} capacitor. The device starts to operate when V _{DD} exceeds 13.5V.
3	DMAG	Demagnetization Sense. This pin is used to detect resonant valleys for QR switching. It also detects the output voltage information, as well as the input voltage information for Brown-in & Brown-out protection.
4	FB	Feedback. Input for the internal PWM comparator.
Body	GND	Ground. Source of Power FET and IC supply ground. Metal pad on bottom of package.

10. Functional Description

The following functional description contains additional information regarding the IC operating modes and pin functionality.

Basic Operation

NV956x family ICs are offline flyback regulators which operate in frequency limit quasi-resonant (QR) mode to reduce switching losses and EMI (electromagnetic interference). It regulates the output based on the load condition through feedback circuitry.

The QR resonant frequency is determined by the transformer primary inductance (L_p) and the primary side GaN FET effective output capacitance ($C_{oss-eff}$).

$$C_{oss-eff} = C_{oss-GaN FET} + C_{parasitic} + C_{transformer} \quad (\text{Equation 1})$$

$$t_{resonance} = 2\pi \sqrt{L_p \times C_{oss-eff}} \quad (\text{Equation 2})$$

In a general 956x design at no load or light load condition, the frequency limit f_{S_BNK} for the pulse-to-pulse operating frequency is f_{S_TMO} . So operating frequency is between f_{S_TMO} and $1/(1/f_{S_TMO} + t_{resonance})$. At the medium load condition (e.g. 25%~50% of full load), the frequency limit f_{S_BNK} is modulated as a function of load condition such that it varies between f_{S_TMO} and $f_{S_BNK_MAX_LL(HL)}$ as load varies. At the heavy load condition (e.g. 50%~100% of full load), f_{S_BNK} is fixed at $f_{S_BNK_MAX_LL(HL)}$ such that the switching frequency is not higher than $f_{S_BNK_MAX}$ as shown in the figure below.

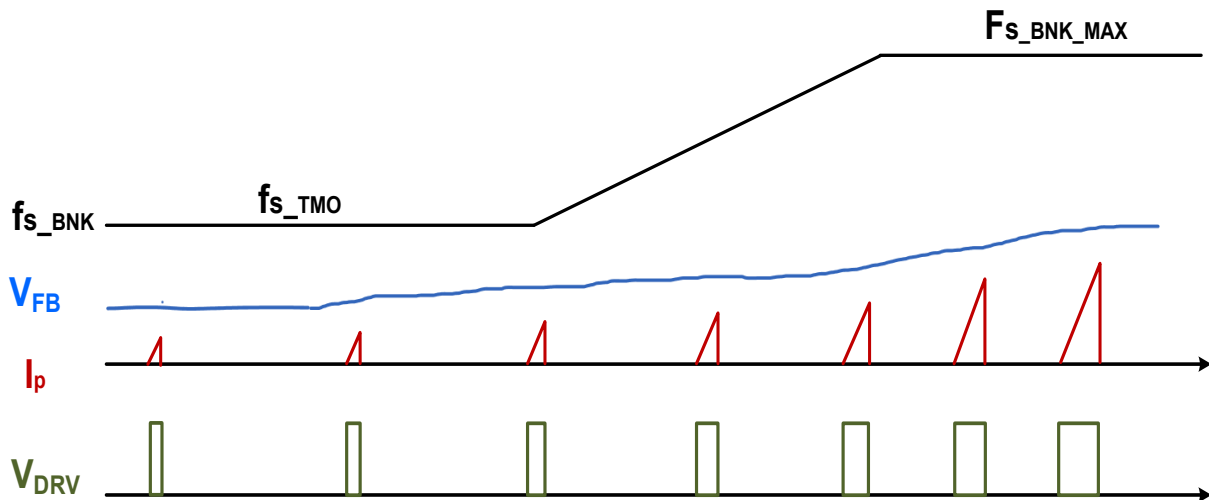


Figure 20 Frequency Fold-Back Operation

NV956x family ICs also have option to operate in CCM at low line. When the device enters CCM, the maximum CCM frequency limit is $f_{S_BNK_MAX_CCM}$.

Burst Mode

As shown in Figure 21, when feedback voltage V_{FB} drops below $V_{FB_BST_ENT}$ at light load, the PWM output shuts off and the output voltage drops at a rate depending on current level of the load. Thereafter, the voltage of feedback- V_{FB} rises. Once V_{FB} exceeds $V_{FB_BST_EXT}$, NV956x family products resume switching and the switch peak currents is limited by V_{CS_MIN} . If more power is delivered to the load than required, V_{FB} voltage will decrease. Once V_{FB} voltage is pulled below $V_{FB_BST_ENT}$, switching stops again. In this manner, the burst mode operation alternately enables and disables switching of the GaN FET to regulate the output and in the meanwhile reduce the switching losses.

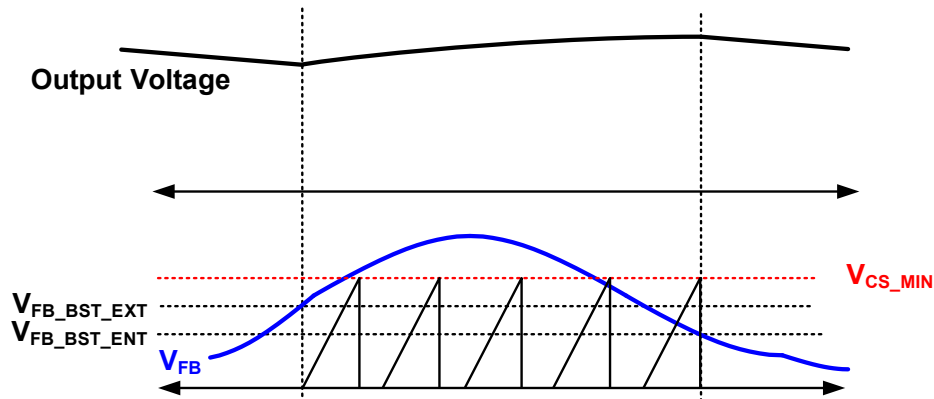


Figure 21 Burst Mode Operation

Deep Green Mode

NV956x family ICs enter the deep green mode if V_{FB} voltage stays below $V_{FB_BST_ENT}$ for more than t_{D_DPGN} . In the deep green mode, the IC operating current is reduced to I_{DD_DPGN} to minimize power consumption. IC resumes switching with normal operating current I_{DD_OP} once V_{FB} voltage rises above $V_{FB_BST_EXT}$.

Valley Detection

NV956x family valley detection is achieved by monitoring V_{DMAG} voltage, which is the divided auxiliary winding voltage by R_{DMAG1} and R_{DMAG2} as shown in figure below. One ceramic capacitor (C_{DMAG}) with typical value of 10pF (and not bigger than 22pF) is recommended to filter out the noise if there is PCB noise coupling concern.

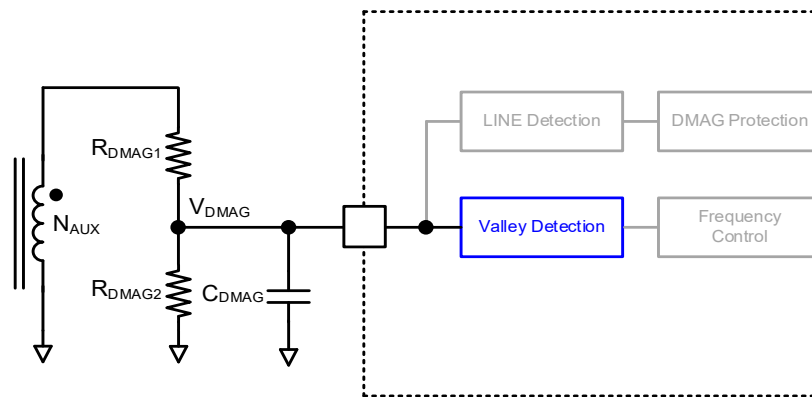


Figure 22 Valley Detection Circuit

Frequency Jitter

To help system to meet stringent EMI requirements, NV956x features advanced frequency jittering to average the energy peaks over the EMI frequency range.

Output Voltage Detection

NV956x family products detect output voltage through DMAG voltage. The figure below shows the DMAG voltage ($V_{DMAG-S/H}$) sampled at the end of t_{DMAG_BNK} to avoid sampling errors. The DMAG voltage is set based on the transformer turn ratio, the voltage divider resistors R_{DMAG1} & R_{DMAG2} . The ratio ($Ratio_{DMAG}$) between $V_{DMAG-S/H}$ and V_o can be defined as:

$$Ratio_{DMAG} = \frac{V_{DMAG-S/H}}{V_o} = \frac{N_A}{N_S} \times \frac{R_{DMAG2}}{R_{DMAG1} + R_{DMAG2}} \quad (\text{Equation 3})$$

$Ratio_{DMAG}$ is required to be designed to guarantee V_o nominal operation will not hit protection, i.e., $V_{DMAG-S/H}$ will not hit either $V_{DMAG-OVP}$ or $V_{DMAG-UVLP}$ described in protection section. For USB-PD/PPS applications, a typical recommended $Ratio_{DMAG}$ design is 0.16.

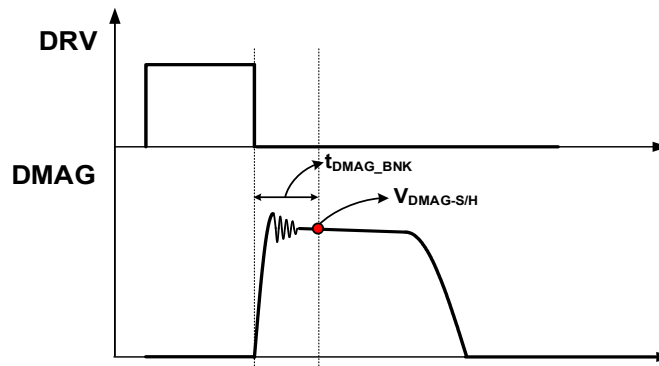


Figure 23 Output Voltage Detection

Line Voltage Detection

As illustrated in Figure 24, NV956X family products indirectly sense the line voltage through DMAG pin during GaN FET turn-on period. During the GaN FET conduction time, the line voltage detector clamps DMAG pin voltage at 0V. The auxiliary winding voltage, V_{AUX} , is proportional to the input bulk capacitor voltage, V_{BLK} . So current I_{DMAG} flowing out of DMAG pin is expressed as:

$$I_{DMAG} = \frac{V_{BLK}}{R_{DMAG1}} \times \frac{N_A}{N_P} \quad (\text{Equation 4})$$

I_{DMAG} current, reflecting the line voltage information, is used for the brown-in and brown-out protection.

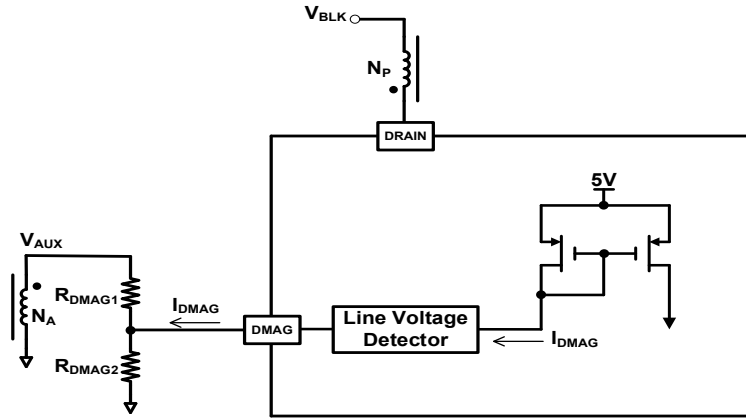


Figure 24 Line Voltage Detection Circuit

LPS Function

NV956X family products incorporate built-in circuits to limit output power and limit output current in the event of the protocol IC becoming malfunction.

HV Start-up

During startup, the internal HV startup circuit is enabled, and the input voltage supplies the current, I_{HV} , from drain pin to charge hold-up capacitor C_{VDD} . When V_{DD} voltage reaches V_{DD_ON} , the HV startup circuit is disabled. The IC starts PWM switching and senses DMAG signal to check the brown-in condition. If the brown-in is not detected, the IC enters the auto-restart mode. The HV startup circuit is connected to the Drain pin

Protection Description

NV956X family products protection functions include VDD over-voltage protection (VDD-OVP), Brown-out protection, DMAG over-voltage protection (DMAG-OVP), DMAG under-voltage protection (DMAG-UVP), IC internal over-temperature protection (OTP). All protections have auto-restart and long auto-restart mode. The selected option information is provided on page 3.

When the long auto-restart mode protection is triggered, the integrated GaN FET is turned off for a time period of t_{VDD_LAR} . After t_{VDD_LAR} , if VDD rises above V_{DD_ON} , NV956X family products resume normal operation as shown in the figure below.

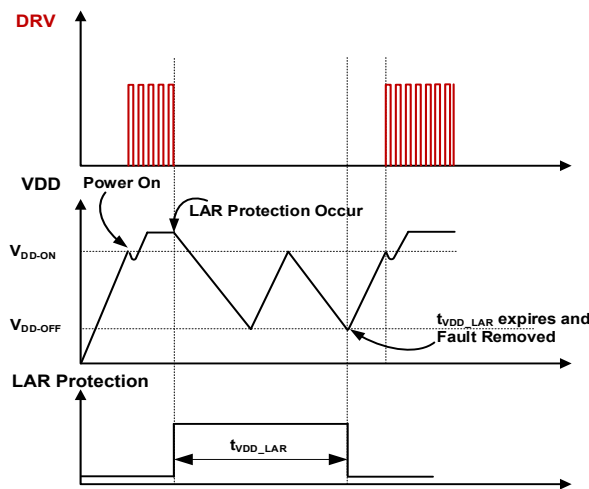


Figure 25 Auto-Restart Long AR Mode

VDD-OVP

VDD-OVP prevents IC damage from over voltage stress when abnormal system conditions occur. When VDD voltage exceeds V_{DD_OVP} for the debounce time $t_{D_VDD_OVP}$, the VDD-OVP protection is triggered, the device enters protection mode.

Brown-in & Brown-out

The sensed line voltage information is used for the brown-in and brown-out protection. During GaN FET conduction time, when the current I_{DMAG} flowing out of DMAG pin is higher than I_{DMAG_BRI} for N_{BRI} debounce cycles, the brown-in is enabled. The input bulk capacitor voltage level to enable the brown-in is given as

$$V_{BLK_Brownin} = I_{DMAG_BRI} \times \frac{R_{DMAG1}}{N_A/N_P} \quad \text{(Equation 5)}$$

When I_{DMAG} is lower than I_{DMAG_BRO} for longer than t_{D_BRO} , the brown-out is triggered. The input bulk capacitor voltage level to trigger the brown-out protection is given as

$$V_{BLK_Brownout} = I_{DMAG_BRO} \times \frac{R_{DMAG1}}{N_A/N_P} \quad \text{(Equation 6)}$$

IC Internal OTP

The internal temperature-sensing circuit disables the PWM output if the junction temperature exceeds T_{OTP} , and the IC enters protection mode.

DMAG-OVP

DMAG-OVP prevents server system damage when abnormal system conditions occur and cause DMAG voltage to rise abnormally. Usually, DMAG over voltage protection is caused by not working properly feedback network (FB) or a fault condition of the DMAG voltage divider resistors. Figure below shows the internal circuit of DMAG-OVP. When abnormal system conditions occur and cause DMAG voltage to exceed V_{DMAG_OVP} for more than N_{DMAG_OVP} consecutive switching cycles, PWM pulses are disabled, and the IC enters protection mode.

For DMAG voltage divider design, R_{DMAG1} is obtained from Equation 5, and R_{DMAG2} is determined by Equation 3. The output over voltage protection level, V_{O_OVP} , can be determined by Equation 7.

$$V_{O_OVP} = \frac{N_S}{N_A} \times \left(1 + \frac{R_{DMAG1}}{R_{DMAG2}}\right) \times V_{DMAG_OVP} \quad \text{(Equation 7)}$$

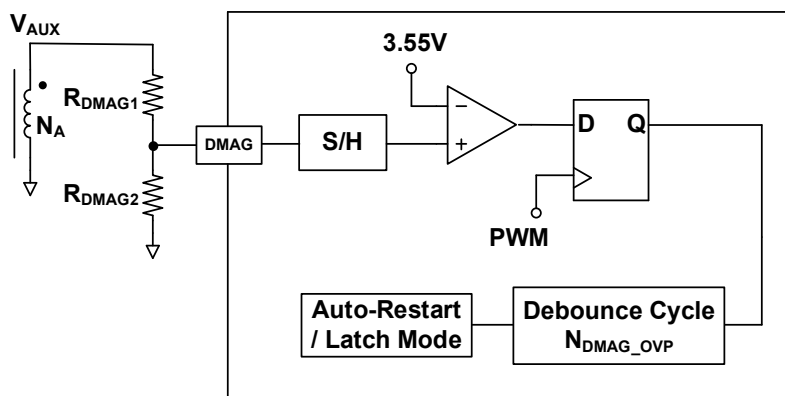


Figure 26 DMAG Over Voltage Protection Circuit

DMAG-UVP

In the event with short output, the output voltage will drop, and the primary peak current will increase. To prevent operation for a long time under this condition, NV956x family products incorporate the under-voltage protection through DMAG pin (DMAG-UVP). The figure below shows the internal circuit for DMAG-UVP. When DMAG voltage is less than V_{DMAG_UVP} and longer than de-bounce cycles N_{DMAG_UVP} , DMAG UVP is triggered, and the IC enters protection mode.

The output under voltage protection level, V_{O_UVP} , can be determined by Equation 8.

$$V_{O_UVP} = \frac{V_{DMAG_UVP}}{Ratio_{DMAG}} = \frac{N_S}{N_A} \times \left(1 + \frac{R_{DMAG1}}{R_{DMAG2}}\right) \times V_{DMAG_UVP} \tag{Equation 8}$$

To avoid DMAG-UVP triggering during the startup sequence, startup blanking time $t_{VDMAG_UVP_BNK}$ is incorporated for system power on.

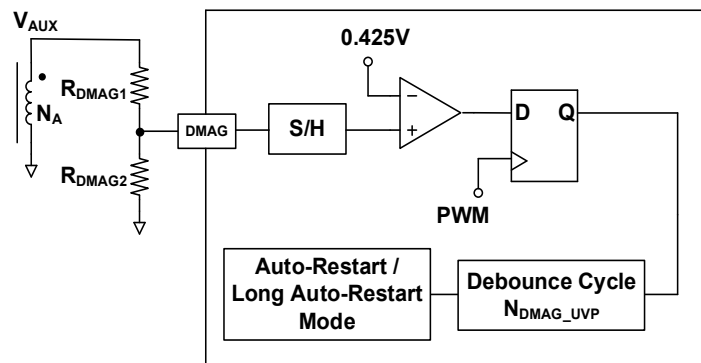


Figure 27 DMAG Under Voltage Protection Circuit

Cycle by Cycle Current Limit

Under certain operation conditions, such as the startup or the overload condition, the feedback control loop can be saturated and is unable to control the primary peak current. To limit the current under such conditions, NV956X family products incorporate the cycle-by-cycle current protection which forces the GaN switch turn off when power FET current reaches the current limit I_p .

GaN Power FET Drain-to-Source Voltage Considerations

GaN Power ICs have been designed and tested to provide significant design margin to handle transient and continuous voltage conditions that are commonly seen in single-ended topologies, such as quasi-resonant (QR) flyback applications. The different voltage levels and recommended margins in a typical QR flyback can be analyzed using Fig. 33. When the device is switched off, the energy stored in the transformer leakage inductance will cause V_{DS} to overshoot to the level of V_{SPIKE} . The clamp circuit should be designed to control the magnitude of V_{SPIKE} . After dissipation of the leakage energy, the device V_{DS} will settle to the level of the bus voltage plus the reflected output voltage which is defined in the figure below as V_{DS-OFF} .

- For repetitive events, 80% derating should be applied from $V_{DS(TRAN)}$ rating (800V) to 640V max under the worst-case operating conditions.
- It is recommended to design the system such that V_{DS-OFF} is derated 80% from the $V_{DS(CONT)}$ (700V) max rating to 560V.
- For half-bridge-based topologies, such as LLC, V_{DS} voltage is clamped to the bus voltage. V_{DS} should be designed such that it meets the V_{DS-OFF} derating guideline (560V).
- Non-repetitive events are infrequent, one-time conditions such as line surge, ESD, and lightning. No derating from the $V_{DS(TRAN)}$ rating (800V) is needed for non-repetitive V_{SPIKE} durations $< 100 \mu s$. The $V_{DS(TRAN)}$ rating (800V) allows for repetitive events that are $< 400 ns$, with 80% derating required (for example repetitive leakage inductance spikes).

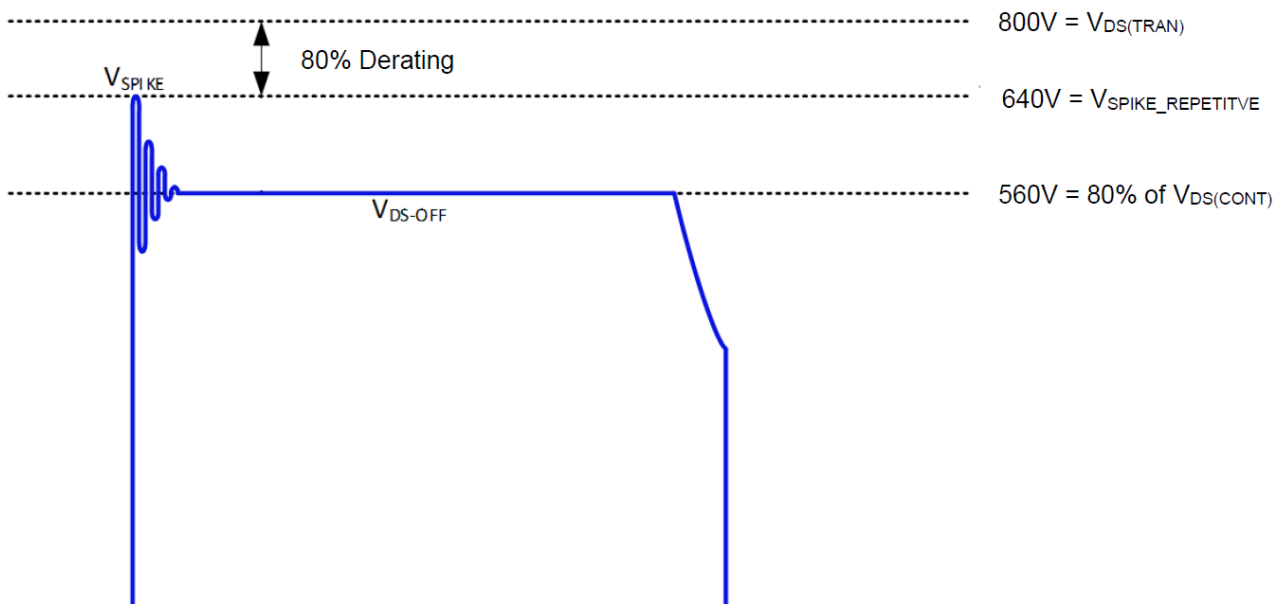
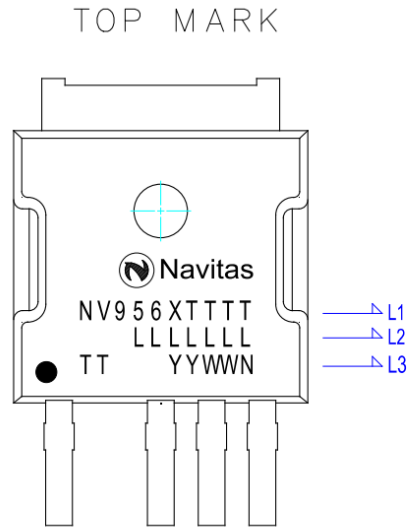


Figure 28 QR flyback drain-to-source voltage stress diagram

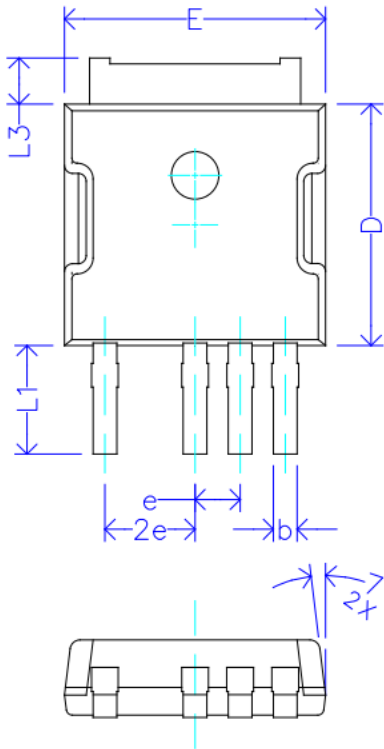
11. Package Outline (DPAK-4L)



Marking Line	Marking Symbol	Content Description
L1	NV956XTTTT	Part Number : First 10 digits of part number, where TTTT trim code of device. (If device name is 12 digits, last 2 digits for special parts will be printed in the 3rd line TT where is bank for general parts)
L2	LLLLLLL	Lot Number : Max 7 digits assembly lot number for marking Example : NC31900
L3	TT	Optional Trim Code : Last 2 digits of device name incase device name is 12 digits
	YY	Year Code : Last 2 digits of the year Example : 2023, YY=23
	WW	Week Code : 01 - 53
	N	Supplier Site Code : Y = HYME

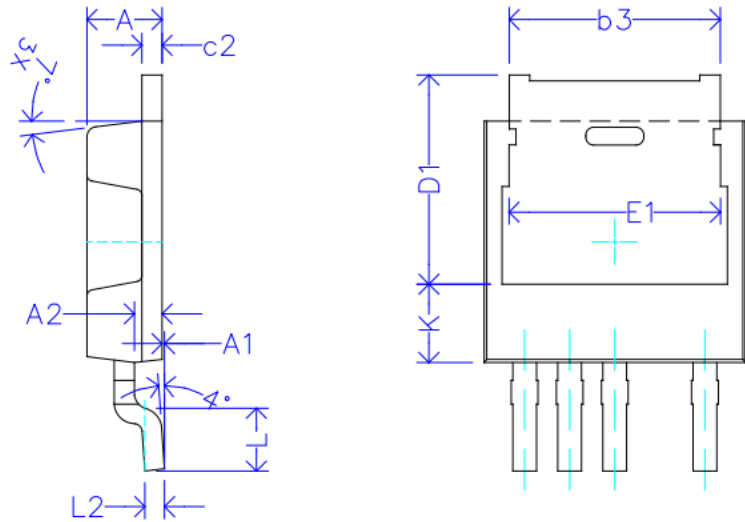
11. Package Outline (Cont.)

TOP VIEW



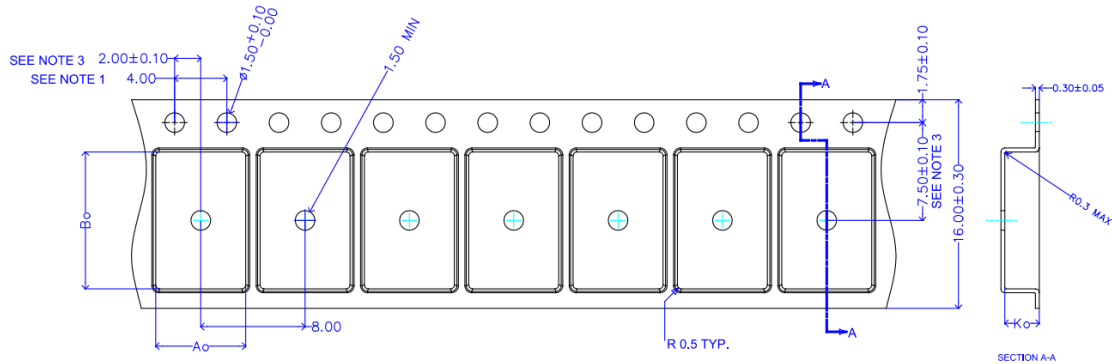
SYMBOL	MIN	NOM	MAX
A	1.80	1.90	2.00
A1	0.00	-	0.20
A2	0.60	0.70	0.80
b	0.508	0.60	0.711
b3	5.21	-	5.46
c2	0.41	0.508	0.61
D	6.00	6.10	6.22
D1	4.90	-	-
E	6.40	6.60	6.73

BOTTOM VIEW



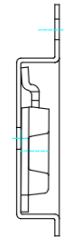
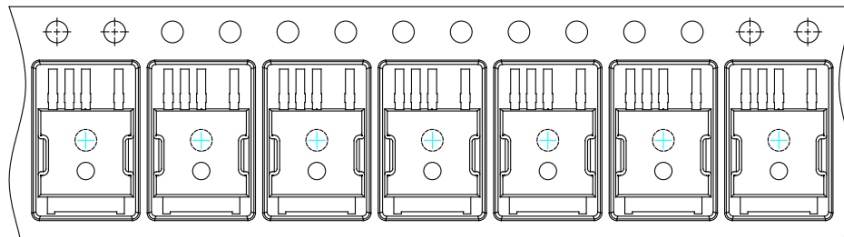
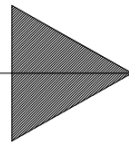
SYMBOL	MIN	NOM	MAX
E1	5.10	5.30	5.50
e		1.14 BSC	
L	1.34	1.585	1.77
L1		2.743 REF	
L2	0.41	0.508	0.61
L3	0.88	-	1.28
K	1.98	-	-
Package Draft Angles	5-9 degrees		
Foot Angle	0-8 degrees		
Gauge Plane for L	0.508		
Notes :			
1. All dimensions in mm.			
2. Reference JEDEC TO-252F VAR AD			
3. 100% Sn Plating			

12. Tape and Reel Dimensions



Notes	
Ao	6.9
Bo	10.50
Ko	2.65
1. 10 sprocket hole pitch cumulative tolerance ± 0.2	
2. Camber in compliance with EIA 481	
3. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.	

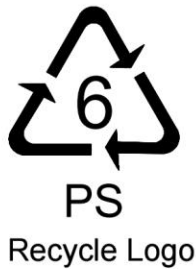
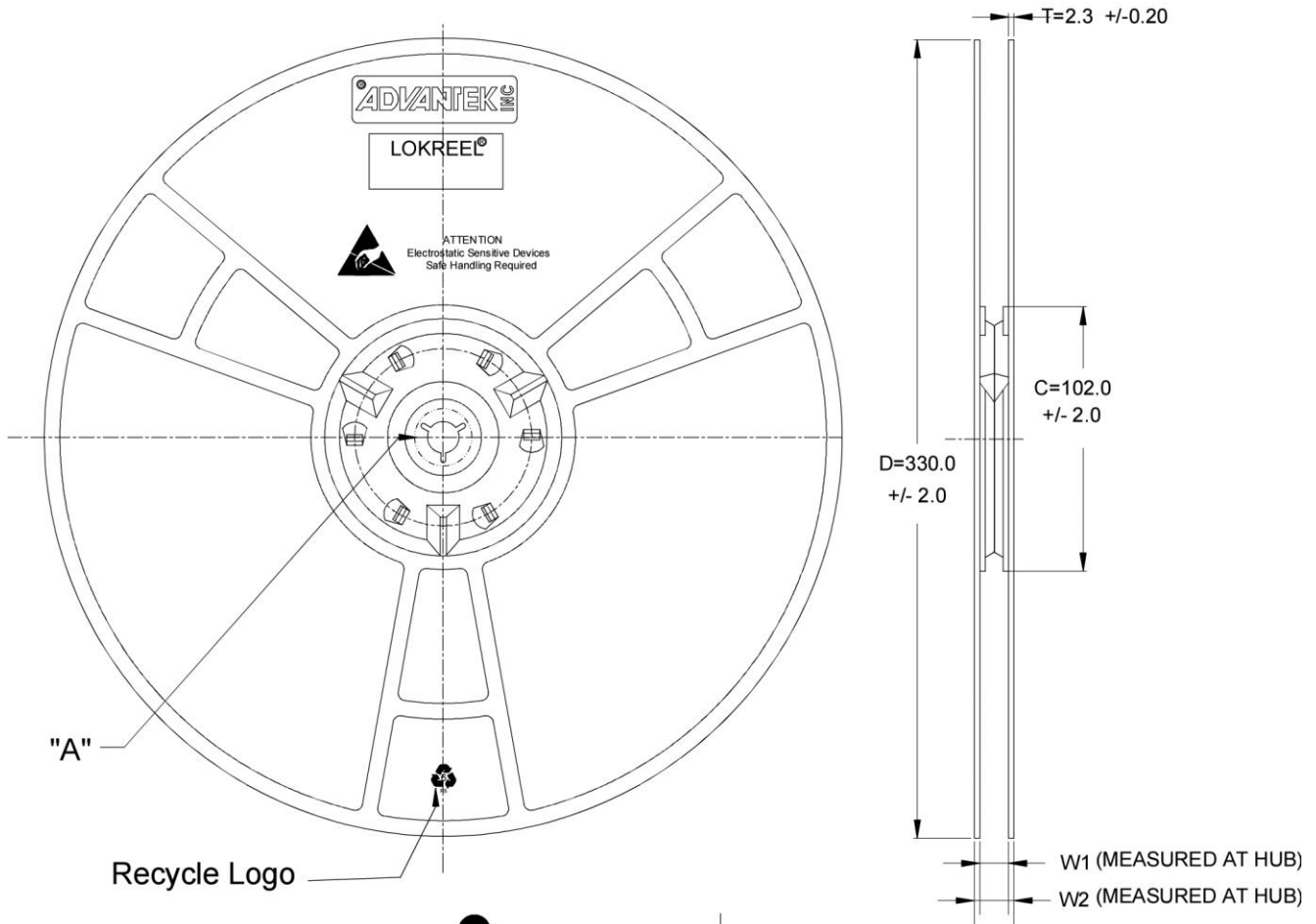
**FEED
DIRECTION**



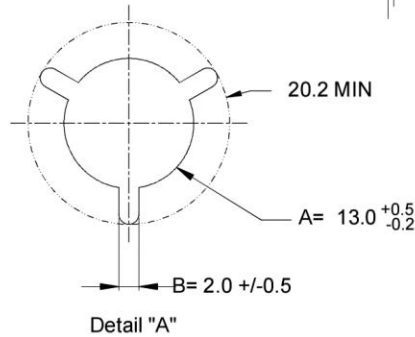
Reel Quantity		Pin 1 Orientation						
Reel Size	Unit qty in reel	<table border="1"> <tr> <td>2</td> <td>1</td> <td rowspan="2">Pin 1 on quadrant 1</td> </tr> <tr> <td>3</td> <td>4</td> </tr> </table>	2	1	Pin 1 on quadrant 1	3	4	
2	1		Pin 1 on quadrant 1					
3	4							
13 "	2500 units							
Leader and trailer pocket : 50 empty pockets								

12. Tape and Reel Dimensions (Cont.)

-All Dimensions in Millimeters-



Recycle Logo



Note:

1. RB: Re grind Blue Lokreel
2. RBK: Re grind Black Lokreel
3. RC: Conductive Lokreel
4. SW: White Lokreel
5. SW-BL: Blue Lokreel
- 5.1 Suffix "DBK" : Black Reel ; 1x 10 Exp 5 < SR < 1 x 10 Exp 10 ohms/sq.
6. RD Series Lokreel: 1x 10 Exp 5 < SR < 1 x 10 Exp 12 ohms/sq.
7. RC Series Lokreel: SR < 1 x 10 Exp 5 ohms/sq.

Nominal Hub Width	W1	W2 MAX
12mm	12.8mm +1.6 / -0.4	18.4mm

13. 20-Year Limited Product Warranty

The 20-year limited warranty applies to all packaged Navitas GaNFast Power ICs and GaNSense HFQR Controllers in mass production, subject to the terms and conditions of, Navitas' express limited product warranty, available at <https://navitassemi.com/terms-conditions>. The warranted specifications include only the MIN and MAX values only listed in Absolute Maximum Ratings and Electrical Characteristics sections of this datasheet. Typical (TYP) values or other specifications are not warranted.



14. Revision History

Date	Status	Notes
10-11-2025	Datasheet	First publication

Additional Information

DISCLAIMER Navitas Semiconductor (Navitas) reserves the right to modify the products and/or specifications described herein at any time and at Navitas' sole discretion. All information in this document, including descriptions of product features and performance, is subject to change without notice. Performance specifications and the operating parameters of the described products are determined in the independent state and are not guaranteed to perform the same way when installed in customer products. The information contained herein is provided without representation or warranty of any kind, whether express or implied. This document is presented only as a guide and does not convey any license under intellectual property rights of Navitas or any third parties. Navitas' products are not intended for use in applications involving extreme environmental conditions or in life support systems. [Terms and Conditions](#). Navitas Semiconductor, Navitas, GaNFast, GaNSense and associated logos are registered trademarks of Navitas.

Copyright ©2023 Navitas Semiconductor. All rights reserved

Contact info@navitassemi.com

